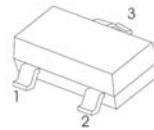


SOT-23 Plastic-Encapsulate MOSFETS

UMW AO3415A P-Channel 20-V(D-S) MOSFET

V_{(BR)DSS}	R_{DS(on)MAX}	I_D
-20 V	36mΩ@-4.5V	-4A
	60mΩ@-2.5V	

SOT-23



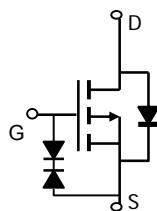
FEATURE

- Excellent R_{DS(ON)}, low gate charge, low gate voltages

APPLICATION

- Load switch and in PWM applications

Equivalent Circuit

Maximum ratings (T_a=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	-20	V
Gate-Source Voltage	V _{GS}	±8	
Continuous Drain Current (t≤10s)	I _D	-4.0	A
Maximum Power Dissipation (t≤10s)	P _D	0.35	W
Thermal Resistance from Junction to Ambient	R _{θJA}	357	°C/W
Operating Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55 ~+150	°C

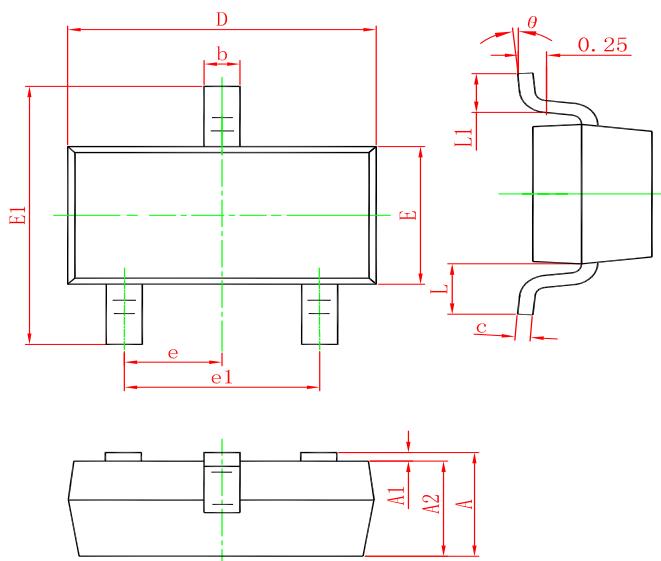
SOT-23 Plastic-Encapsulate MOSFETS

T_a=25 °C unless otherwise specified

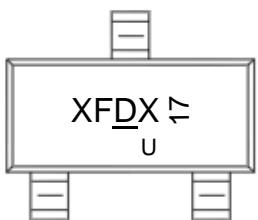
Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static Parameters						
Drain-source breakdown voltage	V _{(BR) DSS}	V _{GS} = 0V, I _D = -250µA	-20			V
Gate threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250µA	-0.3	-0.56	-1	
Gate-body leakage current	I _{GSS}	V _{DS} = 0V, V _{GS} = ±8V			±10	µA
		V _{DS} = 0V, V _{GS} = ±4.5V			±1	
Zero gate voltage drain current	I _{bss}	V _{DS} = -16V, V _{GS} = 0V			-1	
Drain-source on-state resistance(note1)	R _{DS(on)}	V _{GS} = -4.5V, I _D = -4A		34	36	mΩ
		V _{GS} = -2.5V, I _D = -4A		43	60	
Forward transconductance(note2)	g _{FS}	V _{DS} = -5V, I _D = -4A	8			S
Body diode voltage(note2)	V _{SD}	I _S = -1A, V _{GS} = 0V			-1	V
Dynamic Parameters (note3)						
Input capacitance	C _{iss}	V _{DS} = -10V, V _{GS} = 0V, f = 1MHz		1450		pF
Output capacitance	C _{oss}			205		
Reverse transfer capacitance	C _{rss}			160		
Gate resistance	R _g	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz		6.5		Ω
Switching Parameters						
Total gate charge	Q _g	V _{DS} = -10V, V _{GS} = -4.5V, I _D = -4A		17.2		nC
Gate-Source charge	Q _{gs}			1.3		
Gate-drain charge	Q _{gd}			4.5		
Turn-on delay time (note3)	t _{d(on)}	V _{DS} = -10V, V _{GS} = -4.5V R _{GEN} = 3Ω, R _L = 2.5Ω, t _{d(off)} = 1ns		9.5		ns
Turn-on rise time(note3)	t _r			17		
Turn-off delay time(note3)	t _{d(off)}			94		
Turn-off fall time(note3)	t _f			35		

Notes:

1. Repetitive rating,pulse width limited by junction temperature.
2. Pulse Test : Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
3. These parameters have no way to verify.

SOT-23 PACKAGE OUTLINE DIMENSIONS

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Marking**Ordering information**

Order code	Package	Baseqty	Deliverymode
UMW AO3415A	SOT-23	3000	Tape and reel

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